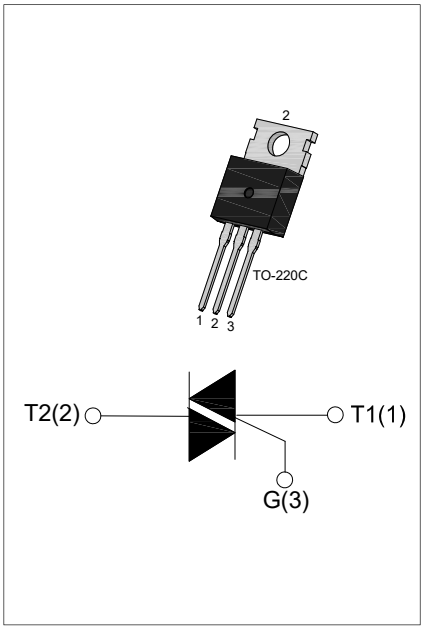
JST16C-800CW 16A TRIAC

Rev.2

DESCRIPTION:

With high ability to withstand the shock loading of large current, JST16C-800CW triac provide high dv/dt rate with strong resistance to electromagnetic interface. With high commutation performances, especially recommended for use on inductive load. complying with UL standards (File ref: E252906). Package TO-220C is RoHS compliant. (2011/65/EU)



MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	16	A
V_{DRM} /V_{RRM}	800	V

ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Storage junction temperature range		T_{stg}	-40-150	℃
Operating junction temperature range		T_j	-40-125	℃
Repetitive peak off-state voltage (T_j=25℃)		V_{DRM}	800	V
Repetitive peak reverse voltage (T_j=25℃)		V_{RRM}	800	V
Non repetitive surge peak Off-state voltage		V_{DSM}	V_{DRM} +100	V
Non repetitive peak reverse voltage		V_{RSM}	V_{RRM} +100	V
RMS on-state current	TO-220C (T_C=100℃)	$I_{T(RMS)}$	16	A
Non repetitive surge peak on-state current (full cycle, F=50Hz)		I_{TSM}	160	A
I^2t value for fusing (tp=10ms)		I^2t	128	A^2s
Critical rate of rise of on-state current (I_G =2×I_{GT})		dI/dt	50	A/μs
Peak gate current tp=20uS		I_{GM}	4	A
Average gate power dissipation		$P_{G(AV)}$	1	W
Peak gate power tp=20uS		P_{GM}	5	W
Peak pulse voltage (Tj=25℃; non-repetitive,off-state;FIG.7)		Vpp	4	kV

ELECTRICAL CHARACTERISTICS (T_j=25℃ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	V_D =12V R_L =33Ω	Ⅰ-Ⅱ-Ⅲ	MAX	35	mA
V_{GT}		Ⅰ-Ⅱ-Ⅲ	MAX	1.3	V
V_{GD}	V_D =V_{DRM} T_j =125℃ R_L =3.3KΩ	Ⅰ-Ⅱ-Ⅲ	MIN	0.2	V
I_L	I_G =1.2I_{GT}	Ⅰ-Ⅲ	MAX	50	mA
		Ⅱ		60	
I_H	I_T =100mA		MAX	40	mA
dv/dt	V_D=2/3V_{DRM} Gate Open T_j =125℃		MIN	1000	V/μs
t_{on}	I_G=40mA I_A=100mA I_R=10mA T_j=25℃		TYP	5	μs
t_{off}			TYP	50	μs

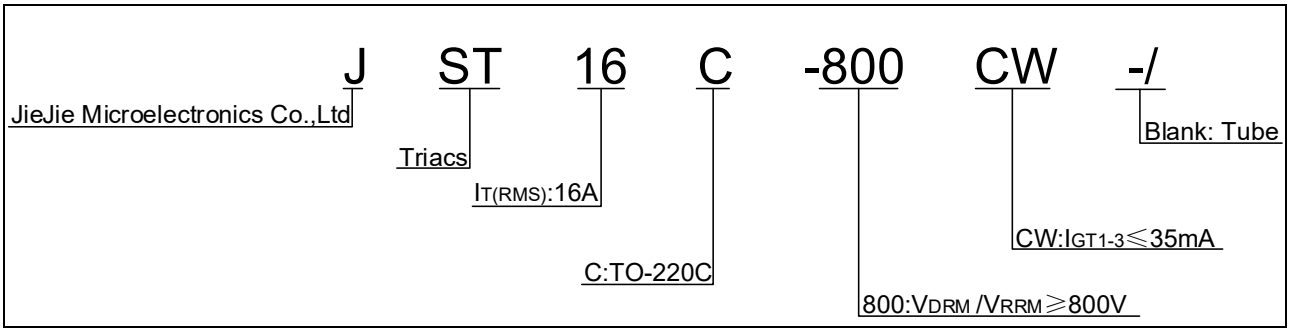
STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
V_{TM}	I_{TM} =22.5A tp=380μs	T_j=25℃	1.5	V
V_{TO}	Threshold voltage	T_j=125℃	0.83	V
Rd	Dynamic resistance	T_j=125℃	17	mΩ
I_{DRM}	V_D =V_{DRM} V_R =V_{RRM}	T_j=25℃	5	μA
I_{RRM}		T_j=125℃	1	mA

THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case(AC)	TO-220C	1.35	℃/W

ORDERING INFORMATION



MARKING

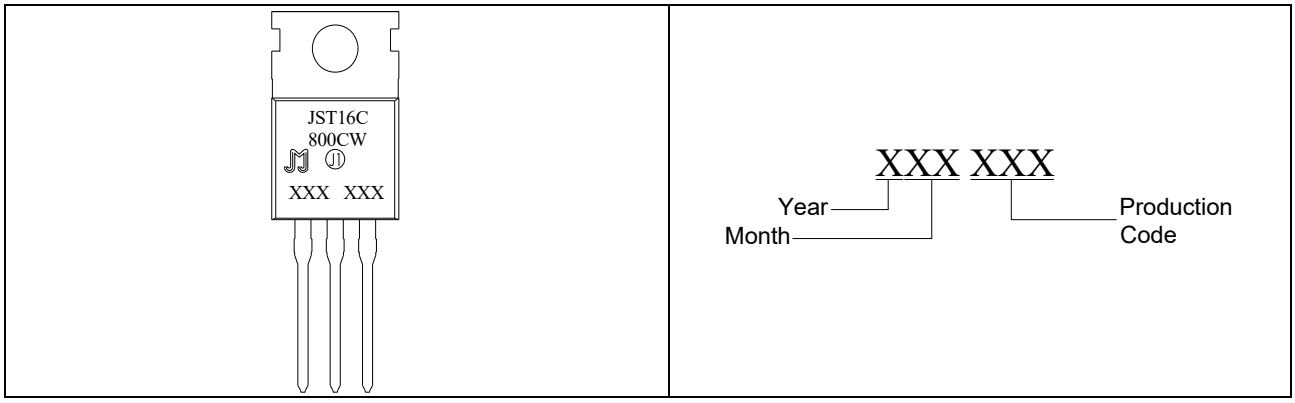


FIG.1: Maximum power dissipation versus RMS on-state current

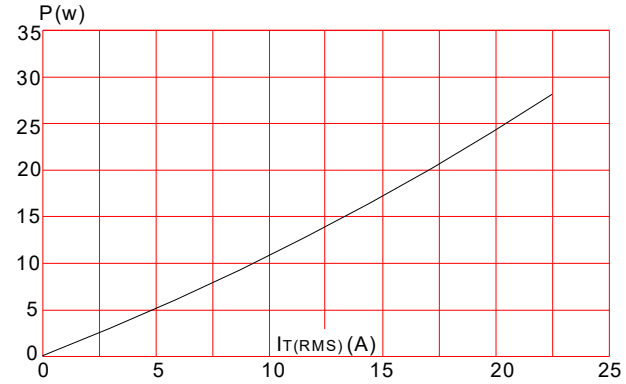


FIG.2: RMS on-state current versus case temperature

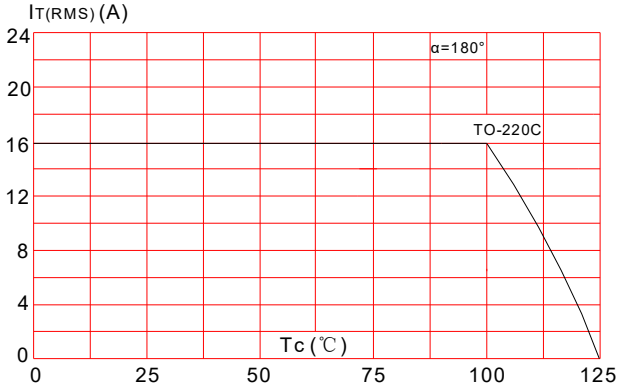


FIG.3: Surge peak on-state current versus number of cycles

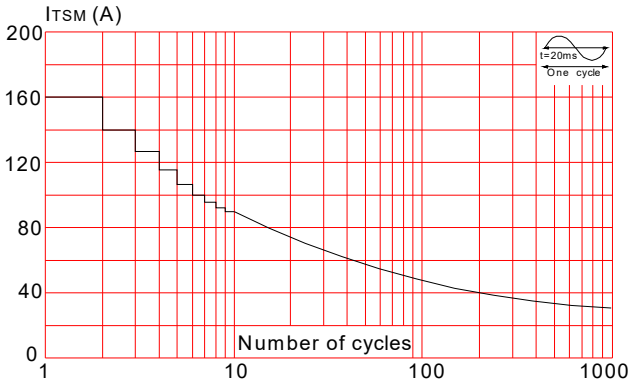


FIG.4: On-state characteristics (maximum values)

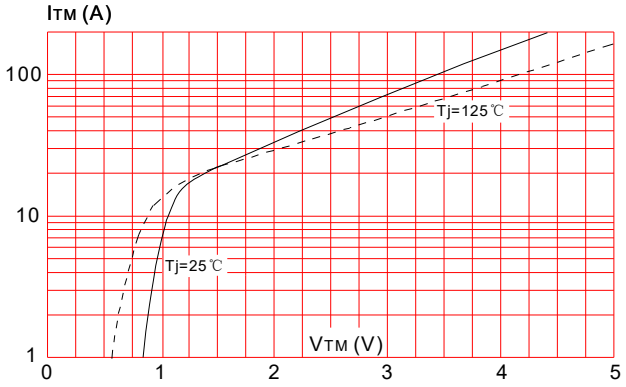


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width tp<20ms, and corresponging value of I^2t (dI/dt < 50A/μs)

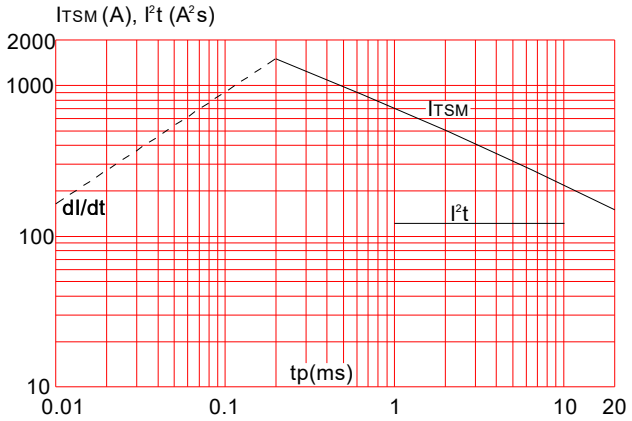


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature

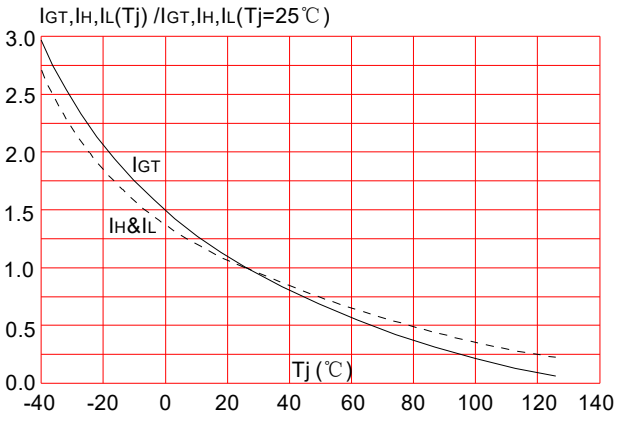
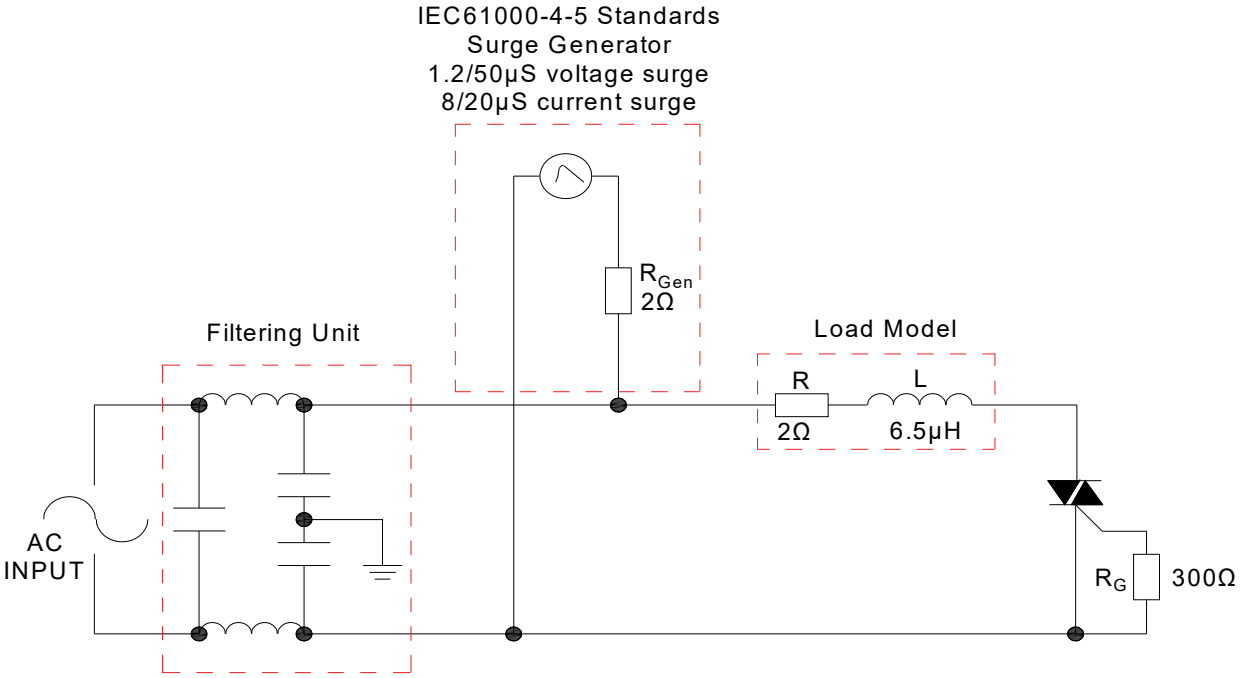


FIG.7：Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



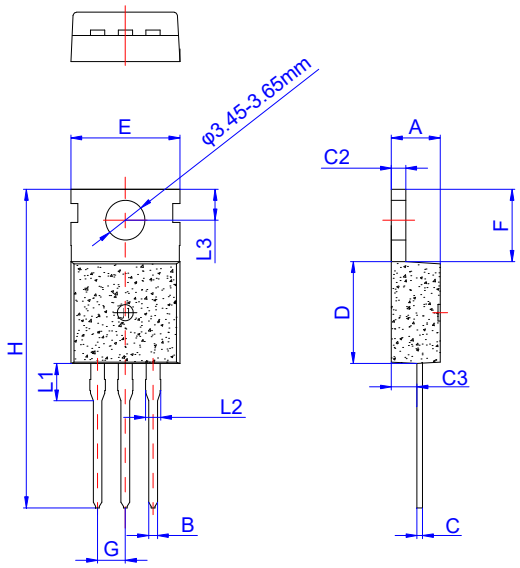
ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JST16C-800CW	**800**	**35**	**TO-220C**	**50**	**Tube**

Document Revision History

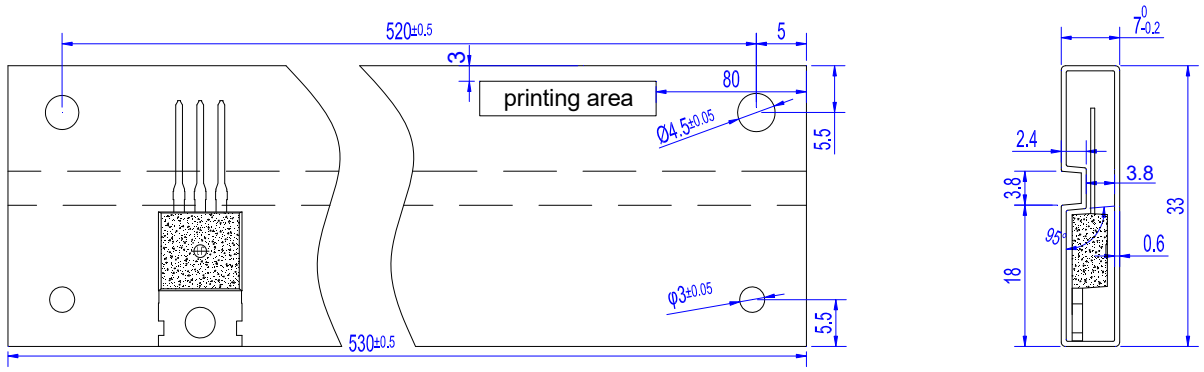
Date	Revision	Changes
Mar 21, 2022	1	Last update
May 27, 2022	2	Add Vpp & t_{on} & t_{off}

PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.70		0.90	0.028		0.035
C	0.45		0.60	0.018		0.024
C2	1.25		1.35	0.049		0.053
C3	2.20		2.60	0.087		0.102
D	8.90		9.90	0.350		0.390
E	9.90		10.3	0.390		0.406
F	6.30		6.90	0.248		0.272
G	2.40		2.70	0.094		0.106
H	28.0		29.8	1.102		1.173
L1	2.70		3.30	0.106		0.130
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116

DELIVERY MODE



PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-220C	TUBE	50	1,000	5,000

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